AlGaAs –Infrared Selective Photodiodes EPD-850-5

(795 - 870 nm) Preliminary data

Description

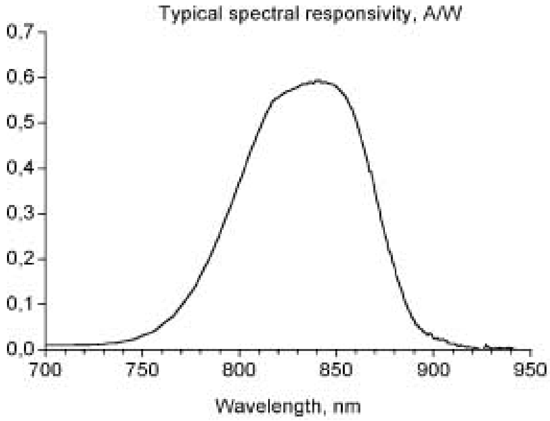
Narrow bandwidth and high spectral sensitivity in the visible range (795…870 nm), low cost chip based on AlGaAs/GaAs, large active areas are possible

Applications

Alarm systems, light barriers, special sensors

Features

Mounted in ∅5 mm standard (T-1 3/4) LED package with different chip sizes



Parameter	Units	Symbol	EPD-850-5/0.4	EPD-850-5/0.5
Chip sizes	mm		0.36 x 0.36	0.46 x 0.46
Active area	mm²	A	0.13	0.12
Typ. dark current at V_R = 5 V	pA	I_D	40	40
Package			T-1 3/4	T-1 3/4
Typ. Spectral range at 0,1 maximum 0,5 maximum	nm	λ_{min}-λ_{max}	760…890 795…870	
Spectral bandwidth at 50%	nm	$\Delta\lambda_{0,5}$	75	
Peak sensitivity wavelength	nm	λ_p	850	
Typical responsivity at λ_p	A/W	$S_{\ddot{e}}$	0.6	
Maximal reverse voltage at I_R=100 µA	V	V_R	10	
Operating temperature range	°C	T_{amb}	-40 to +100	
Storage temperature range	°C	T_{stg}	-40 to +100	

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